

SMALL SIGNAL SCHOTTKY DIODE

VOLTAGE RANGE: 15 V
CURRENT: 30 mA

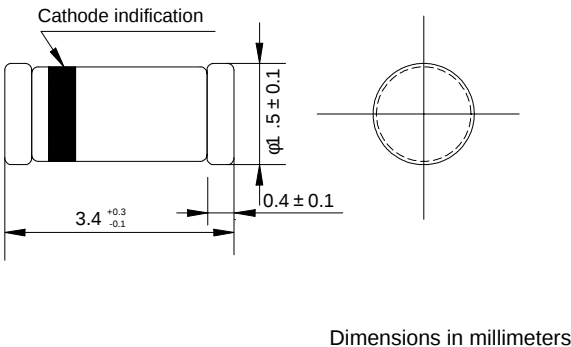
FEATURES

- ◇ For general purpose applications
- ◇ Metal silicon schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications

MECHANICAL DATA

- ◇ Case: JEDEC MINI-MELF, glass case
- ◇ Polarity: Color band denotes cathode end
- ◇ Weight: Approx 0.031 grams

MINI-MELF



ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	UNITS
Peak reverse voltage	V_{RRM}	15	V
Forward continuous current	I_F	30	mA
Surge non repetitive forward current $t_p \leq 1s$	I_{FSM}	60	mA
Junction temperature	T_J	125	°C
Storage temperature range	T_{STG}	-55 ---+ 150	°C
1)Valid provided that electrodes are kept at ambient temperature.			

ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

	Symbols	Min.	Typ.	Max.	UNITS
Reverse breakdown voltage @ $I_R=10 \mu A$	V_R	15			V
Leakage current @ $V_R=6V$	I_R			100	nA
Forward voltage drop @ $I_F=1.0mA$ Test pulse: $t_p \leq 300 \mu s, \delta < 2\%$ $I_F=10mA$ $I_F=30mA$	V_F			0.38 0.5 1.0	V
Junction capacitance @ $V_R=1.0V, f=1MHz$	C_J			1.1	pF
Thermal resistance junction to ambient air	$R_{\theta JA}$			400	K/W

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